Abstracts

Metal-Semiconductor-Metal Photodetectors on Intermediate Temperature MBE Grown GaAs for Lightwave/Millimeter-Wave Applications

A. Paolella, G. Tait, P. Cooke, B. Nabet and B. Tousley. "Metal-Semiconductor-Metal Photodetectors on Intermediate Temperature MBE Grown GaAs for Lightwave/Millimeter-Wave Applications." 1996 MTT-S International Microwave Symposium Digest 96.2 (1996 Vol. II [MWSYM]): 915-918.

Intermediate growth temperature (IGT) GaAs GaAs Metal-Semiconductor-Metal (MSM) photodetectors enables an optimal combination of large dynamic range and speed. In addition these devices are suitable for monolithic integration. The static and temporal response of GaAs MSMs grown by Molecular Beam Epitaxy (MBE) at 350° C has been measured.

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